Shoou Jinn Chang

List of Publications by Year
in descending order

327	4,681	101543	175258
papers	citations	36 h-index	52 g-index

330	330	330	4831
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Highly sensitive ZnO nanowire CO sensors with the adsorption of Au nanoparticles. Nanotechnology, 2008, 19, 175502.	2.6	194
2	A New Tri-Band Bandpass Filter Based on Stub-Loaded Step-Impedance Resonator. IEEE Microwave and Wireless Components Letters, 2012, 22, 179-181.	3.2	119
3	InGaN-AlInGaN multiquantum-well LEDs. IEEE Photonics Technology Letters, 2001, 13, 559-561.	2.5	100
4	Electroluminescence from n-ZnO nanowires/p-GaN heterostructure light-emitting diodes. Applied Physics Letters, 2009, 95, .	3.3	99
5	High Sensitivity of NO Gas Sensors Based on Novel Ag-Doped ZnO Nanoflowers Enhanced with a UV Light-Emitting Diode. ACS Omega, 2018, 3, 13798-13807.	3.5	92
6	Nitride-Based High-Power Flip-Chip LED With Double-Side Patterned Sapphire Substrate. IEEE Photonics Technology Letters, 2007, 19, 780-782.	2.5	75
7	Terahertz temperature-dependent defect mode in a semiconductor-dielectric photonic crystal. Journal of Applied Physics, 2011, 110, .	2.5	72
8	High detectivity InGaN-GaN multiquantum well p-n junction photodiodes. IEEE Journal of Quantum Electronics, 2003, 39, 681-685.	1.9	67
9	High responsivity of amorphous indium gallium zinc oxide phototransistor with Ta2O5 gate dielectric. Applied Physics Letters, 2012, 101, .	3.3	67
10	A High-Responsivity GaN Nanowire UV Photodetector. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 996-1001.	2.9	62
11	ZnO Branched Nanowires and the p-CuO/n-ZnO Heterojunction Nanostructured Photodetector. IEEE Nanotechnology Magazine, 2013, 12, 263-269.	2.0	62
12	A Lateral ZnO Nanowire Photodetector Prepared on Glass Substrate. Journal of the Electrochemical Society, 2010, 157, K30.	2.9	61
13	ZnO Nanowire-Based Oxygen Gas Sensor. IEEE Sensors Journal, 2009, 9, 485-489.	4.7	58
14	Surface Characteristics, Optical and Electrical Properties on Sol-Gel Synthesized Sn-Doped ZnO Thin Film. Materials Transactions, 2010, 51, 1340-1345.	1.2	57
15	Tunable UV- and Visible-Light Photoresponse Based on p-ZnO Nanostructures/n-ZnO/Glass Peppered with Au Nanoparticles. ACS Applied Materials & Interfaces, 2017, 9, 14935-14944.	8.0	57
16	Automated passive filter synthesis using a novel tree representation and genetic programming. IEEE Transactions on Evolutionary Computation, 2006, 10, 93-100.	10.0	55
17	Amorphous InGaZnO ultraviolet phototransistors with double-stack Ga2O3/SiO2 dielectric. Applied Physics Letters, 2013, 102, .	3.3	54
18	Fabrication and Characterization of Coaxial p-Copper Oxide/n-ZnO Nanowire Photodiodes. IEEE Nanotechnology Magazine, 2012, 11, 127-133.	2.0	52

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19	High quality ZnO thin films on InP substrates prepared by radio frequency magnetron sputtering. II. Surface acoustic wave device fabrication. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1995, 13, 385-388.	2.1	50
20	GaN-Based Light-Emitting Diode With Sputtered AlN Nucleation Layer. IEEE Photonics Technology Letters, 2012, 24, 294-296.	2.5	49
21	Vertical Single-Crystal ZnO Nanowires Grown on ZnOâ€‰:â€‰Ga/Glass Templates. IEEE Nanotechnology Magazine, 2005, 4, 649-654.	2.0	47
22	A ZnO nanowire vacuum pressure sensor. Nanotechnology, 2008, 19, 095505.	2.6	47
23	A Solar-Blind eta-Ga$_2$O$_3$ Nanowire Photodetector. IEEE Photonics Technology Letters, 2010, 22, 709-711.	2.5	47
24	Electrical and Optical Characteristics of UV Photodetector With Interlaced ZnO Nanowires. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 990-995.	2.9	45
25	CuO Nanowire-Based Humidity Sensor. IEEE Sensors Journal, 2012, 12, 1884-1888.	4.7	44
26	Design of a Compact Ultra-Wideband Bandpass Filter With an Extremely Broad Stopband Region. IEEE Microwave and Wireless Components Letters, 2016, 26, 392-394.	3.2	44
27	Electrostatic studies of Ï€â€“Ï€ interaction for benzene stacking on a graphene layer. Applied Physics Letters, 2011, 99, .	3.3	41
28	A Visible-Blind TiO2Nanowire Photodetector. Journal of the Electrochemical Society, 2012, 159, J132-J135.	2.9	41
29	Amorphous Indiumâ€“Galliumâ€“Oxide UV Photodetectors. IEEE Photonics Technology Letters, 2015, 27, 2083-2086.	2.5	41
30	Bandgap-Engineered in Indiumâ€“Galliumâ€“Oxide Ultraviolet Phototransistors. IEEE Photonics Technology Letters, 2015, 27, 915-918.	2.5	41
31	Growth of Ga$_{m 2}$O $_{m 3}$ Nanowires and the Fabrication of Solar-Blind Photodetector. IEEE Nanotechnology Magazine, 2011, 10, 1047-1052.	2.0	40
32	${m Ga}_{2}{m O}_{3}$ Nanowire Photodetector Prepared on ${m SiO}_{2}/{m Si}$ Template. IEEE Sensors Journal, 2013, 13, 2368-2373.	4.7	40
33	Field-Emission and Photoelectrical Characteristics of Gaâ€“ZnO Nanorods Photodetector. IEEE Transactions on Electron Devices, 2013, 60, 1905-1910.	3.0	39
34	GaN MSM UV Photodetector With Sputtered AlN Nucleation Layer. IEEE Sensors Journal, 2015, 15, 4743-4748.	4.7	37
35	Carbon Nanotubes With Adsorbed Au for Sensing Gas. IEEE Sensors Journal, 2013, 13, 2423-2427.	4.7	36
36	A WO₃Nanoparticles NO Gas Sensor Prepared by Hot-Wire CVD. IEEE Electron Device Letters, 2017, 38, 266-269.	3.9	36

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37	Ultraviolet/Visible Photodetectors Based on pâ€“n NiO/ZnO Nanowires Decorated with Pd Nanoparticles. ACS Applied Nano Materials, 2019, 2, 6343-6351.	5.0	36
38	Inserting a p-InGaN layer before the p-AlGaN electron blocking layer suppresses efficiency droop in InGaN-based light-emitting diodes. Applied Physics Letters, 2012, 101, 081120.	3.3	35
39	Transparent ZnO-nanowire-based device for UV light detection and ethanol gas sensing on c-Si solar cell. RSC Advances, 2016, 6, 11146-11150.	3.6	35
40	Improved Performance of GaN-Based Blue LEDs With the InGaN Insertion Layer Between the MQW Active Layer and the n-GaN Cladding Layer. IEEE Journal of Quantum Electronics, 2010, 46, 513-517.	1.9	34
41	Visible-Blind Photodetectors With Mg-Doped ZnO Nanorods. IEEE Photonics Technology Letters, 2014, 26, 645-648.	2.5	34
42	Gallium nitride metal-semiconductor-metal photodetectors prepared on silicon substrates. Journal of Applied Physics, 2007, 102, .	2.5	32
43	${m Ga}_{2}{m O}_{3}$/AlGaN/GaN Heterostructure Ultraviolet Three-Band Photodetector. IEEE Sensors Journal, 2013, 13, 3462-3467.	4.7	32
44	A eta-Ga$_{2}$O$_{3}$/GaN Schottky-Barrier Photodetector. IEEE Photonics Technology Letters, 2011, 23, 444-446.	2.5	28
45	ZnO nanowires modified with Au nanoparticles for nonenzymatic amperometric sensing of glucose. Applied Physics Letters, 2014, 104, .	3.3	28
46	The properties of photo chemical-vapor deposition SiO2 and its application in GaN metal-insulator semiconductor ultraviolet photodetectors. Journal of Electronic Materials, 2003, 32, 395-399.	2.2	27
47	Nonenzymatic Glucose Sensor Based on Au/ZnO Coreâ€“Shell Nanostructures Decorated with Au Nanoparticles and Enhanced with Blue and Green Light. Journal of Physical Chemistry B, 2017, 121, 2931-2941.	2.6	27
48	Fast Detection and Flexible Microfluidic pH Sensors Based on Al-Doped ZnO Nanosheets with a Novel Morphology. ACS Omega, 2019, 4, 19847-19855.	3.5	27
49	UV Enhanced Field Emission Performance of Mg-Doped ZnO Nanorods. IEEE Transactions on Electron Devices, 2014, 61, 1541-1545.	3.0	26
50	High Density Novel Porous ZnO Nanosheets Based on a Microheater Chip for Ozone Sensors. IEEE Sensors Journal, 2018, 18, 5559-5565.	4.7	26
51	GaN-Based LEDs With a Chirped Multiquantum Barrier Structure. IEEE Photonics Technology Letters, 2012, 24, 1600-1602.	2.5	25
52	Simple method to design a tri-band bandpass filter using asymmetric SIRs for GSM, WIMAX, and WLAN applications. Microwave and Optical Technology Letters, 2011, 53, 1573-1576.	1.4	24
53	A Flexible ZnO Nanowire-Based Humidity Sensor. IEEE Nanotechnology Magazine, 2012, 11, 520-525.	2.0	24
54	Low-Frequency Noise Characteristics of In-Doped ZnO Ultraviolet Photodetectors. IEEE Photonics Technology Letters, 2013, 25, 2043-2046.	2.5	24

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55	Optimization of the dye-sensitized solar cell performance by mechanical compression. Nanoscale Research Letters, 2014, 9, 523.	5.7	24
56	Nitride-Based Light Emitting Diodes With Textured Sidewalls and Pillar Waveguides. IEEE Photonics Technology Letters, 2006, 18, 2517-2519.	2.5	23
57	Deep UV ${m Ta}_{2}{m O}_{5}$/Zinc-Indium-Tin-Oxide Thin Film Photo-Transistor. IEEE Photonics Technology Letters, 2012, 24, 1018-1020.	2.5	23
58	Photoelectrical and Low-Frequency Noise Characteristics of ZnO Nanorod Photodetectors Prepared on Flexible Substrate. IEEE Transactions on Electron Devices, 2013, 60, 229-234.	3.0	23
59	High Responsivity MgZnO Ultraviolet Thin-Film Phototransistor Developed Using Radio Frequency Sputtering. Materials, 2017, 10, 126.	2.9	23
60	Low-Noise and High-Detectivity GaN UV Photodiodes With a Low-Temperature AlN Cap Layer. IEEE Sensors Journal, 2007, 7, 1289-1292.	4.7	22
61	InGaN/GaN light-emitting diodes with a reflector at the backside of sapphire substrates. Journal of Electronic Materials, 2003, 32, 403-406.	2.2	21
62	A eta-${m Ga}_{2} {m O} _{3}$/GaN Hetero-Structured Solar-Blind and Visible-Blind Dual-Band Photodetector. IEEE Sensors Journal, 2011, 11, 1491-1492.	4.7	21
63	ZnO-Nanowire-Based Extended-Gate Field-Effect-Transistor pH Sensors Prepared on Glass Substrate. Science of Advanced Materials, 2012, 4, 1174-1178.	0.7	21
64	Integration of bandgap-engineered double-stacked channel layers with nitrogen doping for high-performance InGaO TFTs. Applied Physics Letters, 2019, 114, .	3.3	20
65	Nitride-Based LEDs With High-Reflectance and Wide-Angle Ag Mirror${+}$SiO$_{2}$/TiO$_{2}$ DBR Backside Reflector. Journal of Lightwave Technology, 2011, 29, 1033-1038.	4.6	19
66	Influences of surface reconstruction on the atomic-layer-deposited HfO2/Al2O3/n-InAs metal-oxide-semiconductor capacitors. Applied Physics Letters, 2011, 98, 123509.	3.3	19
67	Surface plasmon-enhanced gas sensing in single gold-peapodded silica nanowires. NPG Asia Materials, 2013, 5, e49-e49.	7.9	19
68	Noise Characteristics of ZnO-Nanowire Photodetectors Prepared on ZnO:Ga/Glass Templates. IEEE Sensors Journal, 2007, 7, 1020-1024.	4.7	18
69	Highly Reliable High-Brightness GaN-Based Flip Chip LEDs. IEEE Transactions on Advanced Packaging, 2007, 30, 752-757.	1.6	18
70	An ${({m Al}_{m x}{m Ga}_{1-{m x}})}_{2}{m O}_{3}$ Metal-Semiconductor-Metal VUV Photodetector. IEEE Sensors Journal, 2011, 11, 1795-1799.	4.7	18
71	${m Ga}_{2}{m O}_{3}$/GaN-Based Metal-Semiconductor-Metal Photodetectors Covered With Au Nanoparticles. IEEE Photonics Technology Letters, 2013, 25, 1809-1811.	2.5	18
72	Improved Field Emission Properties of Ag-Decorated Multi-Walled Carbon Nanotubes. IEEE Photonics Technology Letters, 2013, 25, 1017-1019.	2.5	18

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73	High Responsivity Mg_xZn_{1â^'x}O Film UV Photodetector Grown by RF Sputtering. IEEE Photonics Technology Letters, 2015, 27, 978-981.	2.5	18
74	Effects of humidity and ultraviolet characteristics on Î²-Ga₂O₃ nanowire sensor. RSC Advances, 2015, 5, 84776-84781.	3.6	18
75	Thin-Film Transistors With Amorphous Indiumâ€“Gallium-Oxide Bilayer Channel. IEEE Electron Device Letters, 2017, 38, 572-575.	3.9	18
76	Studies of polymer ball type polymer dispersed liquid crystal films. Liquid Crystals, 1996, 21, 19-23.	2.2	17
77	AlGaN/GaN metal-oxide semiconductor heterostructure field-effect transistor with photo-chemical-vapor deposition SiO2 gate oxide. Journal of Electronic Materials, 2003, 32, 407-410.	2.2	17
78	Flicker noise of GaN-based heterostructure field-effect transistors with Si-doped AlGaN carrier injection layer. IEEE Electron Device Letters, 2003, 24, 622-624.	3.9	17
79	Enhanced Field Electron Emission From Zinc-Doped CuO Nanowires. IEEE Electron Device Letters, 2012, 33, 887-889.	3.9	17
80	Photo-Electrical Properties of MgZnO Thin-Film Transistors With High- ${k}$ Dielectrics. IEEE Photonics Technology Letters, 2018, 30, 59-62.	2.5	17
81	Electrical Properties of Indium Aluminum Zinc Oxide Thin Film Transistors. Journal of Electronic Materials, 2018, 47, 6923-6928.	2.2	17
82	High quality ZnO thin films on InP substrates prepared by radio frequency magnetron sputtering. I. Material study. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1995, 13, 381-384.	2.1	16
83	High-Detectivity Nitride-Based MSM Photodetectors on InGaNâ€“GaN Multiquantum Well With the Unactivated Mg-Doped GaN Layer. IEEE Journal of Quantum Electronics, 2007, 43, 1060-1064.	1.9	16
84	CuO-Nanowire Field Emitter Prepared on Glass Substrate. IEEE Nanotechnology Magazine, 2011, 10, 1161-1165.	2.0	16
85	InGaN/GaN Multiquantum-Well Metal-Semiconductor-Metal Photodetectors With Beta-${m Ga}_{2}{m O}_{3}$ Cap Layers. IEEE Sensors Journal, 2013, 13, 1187-1191.	4.7	16
86	Noise Properties of Fe-ZnO Nanorod Ultraviolet Photodetectors. IEEE Photonics Technology Letters, 2013, 25, 2089-2092.	2.5	16
87	GaN-Based Ultraviolet Light Emitting Diodes With Ex Situ Sputtered AlN Nucleation Layer. Journal of Display Technology, 2013, 9, 895-899.	1.2	16
88	Synthesis of CuInS2 quantum dots using polyetheramine as solvent. Nanoscale Research Letters, 2015, 10, 122.	5.7	16
89	GaN-Based Power LEDs With CMOS ESD Protection Circuits. IEEE Transactions on Device and Materials Reliability, 2007, 7, 340-346.	2.0	15
90	Low-Noise and High-Detectivity GaN-Based UV Photodiode With a Semi-Insulating Mg-Doped GaN Cap Layer. IEEE Sensors Journal, 2007, 7, 1270-1273.	4.7	15

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91	High quality GaN-based Schottky barrier diodes. Applied Physics Letters, 2008, 93, 132110.	3.3	15
92	Photoconductive Gain of Vertical ZnO Nanorods on Flexible Polyimide Substrate by Low-Temperature Process. IEEE Sensors Journal, 2011, 11, 3457-3461.	4.7	15
93	GaNâ€based Schottky barrier ultraviolet photodetector with a 5â€pair AlGaNâ€“GaN intermediate layer. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 579-584.	1.8	15
94	Oxygen Partial Pressure Impact on Characteristics of Indium Titanium Zinc Oxide Thin Film Transistor Fabricated via RF Sputtering. Nanomaterials, 2017, 7, 156.	4.1	15
95	Indium Gallium Oxide Thin Film Transistor for Two-Stage UV Sensor Application. ECS Journal of Solid State Science and Technology, 2019, 8, Q3140-Q3143.	1.8	15
96	SiGe heterostructure field-effect transistor using V-shaped confining potential well. IEEE Electron Device Letters, 2003, 24, 69-71.	3.9	14
97	Characterization of AlGaN/GaN Metal- Semiconductor-Metal Photodetectors With a Low-Temperature AlGaN Interlayer. IEEE Sensors Journal, 2009, 9, 723-727.	4.7	14
98	AlGaN/GaN Schottky Barrier Photodetector With Multi-${m Mg}_{m x} {m N} _{m y} $/GaN Buffer. IEEE Sensors Journal, 2009, 9, 87-92.	4.7	14
99	Optoelectronic Characteristics of UV Photodetector Based on ZnO Nanopillar Thin Films Prepared by Sol-Gel Method. Materials Transactions, 2009, 50, 922-925.	1.2	14
100	An investigation of the microstructure, optical and electrical properties of ZITO thin film using the solâ€“gel method. Journal of Sol-Gel Science and Technology, 2010, 54, 347-354.	2.4	14
101	Investigating the Effect of Piezoelectric Polarization on GaN-Based LEDs With Different Quantum Barrier Thickness. Journal of Display Technology, 2013, 9, 206-211.	1.2	14
102	Two-dimensional ZnO nanowalls for gas sensor and photoelectrochemical applications. Electronic Materials Letters, 2014, 10, 693-697.	2.2	14
103	Amorphous InGaZnO Ultraviolet Phototransistors With a Thin Ga₂O₃ Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 125-129.	2.9	14
104	A Simple and Effective Method for Designing Frequency Adjustable Balun Diplexer With High Common-Mode Suppression. IEEE Microwave and Wireless Components Letters, 2015, 25, 433-435.	3.2	14
105	Effect of Oxygen Vacancy Ratio on a GaZTO Solar-Blind Photodetector. Coatings, 2018, 8, 293.	2.6	14
106	Introduction to a New Journal: Applied System Innovation. Applied System Innovation, 2018, 1, 1.	4.6	14
107	A Bifacial SnO₂ Thin-Film Ethanol Gas Sensor. IEEE Electron Device Letters, 2018, 39, 1223-1225.	3.9	14
108	Design of Dual-Band Bandpass Filter With Simultaneous Narrow- and Wide-Bandwidth and a Wide Stopband. IEEE Access, 2019, 7, 147694-147703.	4.2	14

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109	AlGaInP-sapphire glue bonded light-emitting diodes. IEEE Journal of Quantum Electronics, 2002, 38, 1390-1394.	1.9	13
110	Enhanced CMOS performances using substrate strained-SiGe and mechanical strained-Si technology. IEEE Electron Device Letters, 2006, 27, 46-48.	3.9	13
111	Crabwise ZnO Nanowire UV Photodetector Prepared on ZnOâ€‰:â€‰Ga/Glass Template. IEEE Nanotechnology Magazine, 2007, 6, 595-600.	2.0	13
112	The Optimized Geometry of the SiGe HBT Power Cell for 802.11a WLAN Applications. IEEE Microwave and Wireless Components Letters, 2007, 17, 49-51.	3.2	13
113	Improved Carrier Distributions by Varying Barrier Thickness for InGaN/GaN LEDs. Journal of Display Technology, 2013, 9, 239-243.	1.2	13
114	Dark Currents in HgCdTe Photodiodes Passivated with ZnS/CdS. Journal of the Electrochemical Society, 1999, 146, 1540-1545.	2.9	12
115	The Effect of Geometry on the Noise Characterization of SiGe HBTs and Optimized Device Sizes for the Design of Low-Noise Amplifiers. IEEE Transactions on Microwave Theory and Techniques, 2004, 52, 2153-2162.	4.6	12
116	Nitride-based LEDs with MQW active regions grown by different temperature profiles. IEEE Photonics Technology Letters, 2005, 17, 1806-1808.	2.5	12
117	High-Brightness InGaNâ€“GaN Power Flip-Chip LEDs. Journal of Lightwave Technology, 2009, 27, 1985-1989.	4.6	12
118	AlGaN/GaN Schottky Barrier UV Photodetectors With a GaN Sandwich Layer. IEEE Sensors Journal, 2009, 9, 814-819.	4.7	12
119	Impact of stress-memorization technique induced-tensile strain on low frequency noise in n-channel metal-oxide-semiconductor transistors. Applied Physics Letters, 2010, 97, 123501.	3.3	12
120	AlGaN/GaN high electron mobility transistors based on InGaN/GaN multiquantum-well structures. Applied Physics Letters, 2010, 96, .	3.3	12
121	Effect of Growth Pressure of Undoped GaN Layer on the ESD Characteristics of GaN-Based LEDs Grown on Patterned Sapphire. IEEE Photonics Technology Letters, 2011, 23, 968-970.	2.5	12
122	InGaP/GaAs/Ge tripleâ€junction solar cells with ZnO nanowires. Progress in Photovoltaics: Research and Applications, 2013, 21, 1645-1652.	8.1	12
123	UV Enhanced Indium-Doped ZnO Nanorod Field Emitter. IEEE Transactions on Electron Devices, 2013, 60, 3901-3906.	3.0	12
124	Highly stable ITO/Zn2TiO4/Pt resistive random access memory and its application in two-bit-per-cell. RSC Advances, 2018, 8, 17622-17628.	3.6	12
125	High-Speed InGaAs P-I-N Photodetector With Planar Buried Heterostructure. IEEE Transactions on Electron Devices, 2009, 56, 1347-1350.	3.0	11
126	A Deep UV Sensitive ${m Ta}_{2}{m O}_{5}/{m a-IGZO}$ TFT. IEEE Sensors Journal, 2011, 11, 2902-2905.	4.7	11

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127	InGaN Metal-Semiconductor-Metal Photodetectors With Aluminum Nitride Cap Layers. IEEE Journal of Quantum Electronics, 2011, 47, 1107-1112.	1.9	11
128	Magnetooptical Effects in Wave Properties for a Semiconductor Photonic Crystal at Near-Infrared. IEEE Photonics Journal, 2012, 4, 903-911.	2.0	11
129	$etahbox{-}{m Ga}_{2}{m O}_{3}$ Nanowires-Based Humidity Sensors Prepared on GaN/Sapphire Substrate. IEEE Sensors Journal, 2013, 13, 4891-4896.	4.7	11
130	Numerical Simulation of GaN-Based LEDs With Chirped Multiquantum Barrier Structure. IEEE Journal of Quantum Electronics, 2013, 49, 436-442.	1.9	11
131	Electron field emission enhancement of hybrid Cu/CuO nanowires fabricated by rapid thermal reduction of CuO nanowires. RSC Advances, 2015, 5, 54220-54224.	3.6	11
132	Two-bit-per-cell resistive switching memory device with a Ti/MgZnO/Pt structure. RSC Advances, 2015, 5, 88166-88170.	3.6	11
133	Nitride-Based ultraviolet metal-semiconductor-metal photodetectors with a low-temperature GaN layer. Journal of Electronic Materials, 2003, 32, 400-402.	2.2	10
134	Deposition of SiO[sub 2] layers on 4Hâ€“SiC by photochemical vapor deposition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 329.	1.6	10
135	InGaNâ€“GaN MQW Metalâ€“Semiconductorâ€“Metal Photodiodes With Semi-Insulating Mg-Doped GaN Cap Layers. IEEE Photonics Technology Letters, 2007, 19, 846-848.	2.5	10
136	AlGaInP LEDs Prepared by Contact-Transferred and Mask-Embedded Lithography. IEEE Journal of Quantum Electronics, 2010, 46, 1834-1839.	1.9	10
137	AlGaInP-Based LEDs With a ${m p}^{+}$-GaP Window Layer and a Thermally Annealed ITO Contact. IEEE Journal of Quantum Electronics, 2011, 47, 803-809.	1.9	10
138	Influence of Weight Ratio of Poly(4-vinylphenol) Insulator on Electronic Properties of InGaZnO Thin-Film Transistor. Journal of Nanomaterials, 2012, 2012, 1-7.	2.7	10
139	Impact of oxygen annealing on high-k gate stack defects characterized by random telegraph noise. Applied Physics Letters, 2012, 101, 122105.	3.3	10
140	Low-Frequency Noise Characteristics of GaN Schottky Barrier Photodetectors Prepared With Nickel Annealing. IEEE Sensors Journal, 2012, 12, 2824-2829.	4.7	10
141	Dislocation reduction through nucleation and growth selectivity of metal-organic chemical vapor deposition GaN. Journal of Applied Physics, 2013, 113, 144908.	2.5	10
142	Stability Improvement of Nitrogen Doping on IGO TFTs under Positive Gate Bias Stress and Hysteresis Test. ECS Journal of Solid State Science and Technology, 2019, 8, Q3034-Q3040.	1.8	10
143	InGaN/GaN multiple quantum well green light-emitting diodes prepared by temperature ramping. Journal of Electronic Materials, 2003, 32, 419-422.	2.2	9
144	Low interface state density AlGaN/GaN MOSHFETs with photochemical vapor deposition SiO2 layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2355-2359.	0.8	9

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145	GaN Schottky Barrier Photodetectors. IEEE Sensors Journal, 2010, 10, 1609-1614.	4.7	9
146	GaN-Based Power Flip-Chip LEDs With an Internal ESD Protection Diode on Cu Sub-Mount. IEEE Transactions on Advanced Packaging, 2010, 33, 433-437.	1.6	9
147	GaN-Based LEDs With Air Voids Prepared by One-Step MOCVD Growth. Journal of Lightwave Technology, 2011, 29, 2831-2835.	4.6	9
148	GaN-Based LEDs With Sapphire Debris Removed by Phosphoric Etching. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2012, 2, 349-353.	2.5	9
149	AlGaInP-Based LEDs With AuBe-Diffused AZO/GaP Current Spreading Layer. IEEE Journal of Quantum Electronics, 2013, 49, 846-851.	1.9	9
150	Enhanced Field Emission of ${m TiO}_{2}$ Nanowires With UV Illumination. IEEE Electron Device Letters, 2014, 35, 123-125.	3.9	9
151	Failure Mechanism for GaN-Based High-Voltage Light-Emitting Diodes. IEEE Photonics Technology Letters, 2014, 26, 1073-1076.	2.5	9
152	Ultimate Aims and Prospects of Inventions. Inventions, 2016, 1, 1-2.	2.5	9
153	High Stability Flexible Deep-UV Detector Based on All-Oxide Heteroepitaxial Junction. ACS Applied Electronic Materials, 2022, 4, 3099-3106.	4.3	9
154	A Ku-band four-stage temperature compensated PHEMT MMIC power amplifier. Microwave and Optical Technology Letters, 2005, 44, 480-485.	1.4	8
155	Dependence of DC Parameters on Layout and Low-Frequency Noise Behavior in Strained-Si nMOSFETs Fabricated by Stress-Memorization Technique. IEEE Electron Device Letters, 2010, 31, 500-502.	3.9	8
156	${m TiO}_{2}$ Nanowires UV Photodetectors With Ir Schottky Contacts. IEEE Photonics Technology Letters, 2012, 24, 1584-1586.	2.5	8
157	GaN-Based LEDs With Omnidirectional Metal Underneath an Insulating ${m SiO}_{2}$ Layer. IEEE Photonics Technology Letters, 2012, 24, 815-817.	2.5	8
158	Chemical Oxide Interfacial Layer for the High-k-Last/Gate-Last Integration Scheme. IEEE Electron Device Letters, 2012, 33, 946-948.	3.9	8
159	Tunable Multichannel Filter in a Photonic Crystal Containing Semiconductor Photonic Quantum Well. IEEE Photonics Journal, 2012, 4, 283-290.	2.0	8
160	Investigation of zinc-tin-oxide thin-film transistors with varying SnO2 contents. Electronic Materials Letters, 2014, 10, 89-94.	2.2	8
161	GaN-Based LEDs With Rough Surface and Selective KOH Etching. Journal of Display Technology, 2014, 10, 27-32.	1.2	8
162	Synthesis of In₂O₃Nanowires and Their Gas Sensing Properties. IEEE Sensors Journal, 2016, 16, 5850-5855.	4.7	8

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163	Neodymiumâ€doped GaAs lightâ€emitting diodes. Journal of Applied Physics, 1995, 78, 4279-4281.	2.5	7
164	InGaN/GaN multiple-quantum-well dual-wavelength near-white light emitting diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2257-2260.	0.8	7
165	Ultra small self-organized nitride nanotips. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 2496.	1.6	7
166	Ir/Pt Schottky contact oxidation for nitride-based Schottky barrier diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1625-1628.	0.8	7
167	The CL emission observation of the InGaN/GaN MQWs V shaped pits with different superlattices underlayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1639-1641.	0.8	7
168	GaN Metalâ€“Semiconductorâ€“Metal Photodetectors Prepared on Nanorod Template. IEEE Photonics Technology Letters, 2010, 22, 625-627.	2.5	7
169	Origin of Stress Memorization Mechanism in Strained-Si nMOSFETs Using a Low-Cost Stress-Memorization Technique. IEEE Nanotechnology Magazine, 2011, 10, 1053-1058.	2.0	7
170	GaN-Based LEDs With Double Strain Releasing MQWs and Si Delta-Doping Layers. IEEE Photonics Technology Letters, 2012, 24, 1809-1811.	2.5	7
171	Diluted Magnetic Nanosemiconductor: Fe-Doped ZnO Vertically Aligned Nanorod Arrays Grown by Hydrothermal Synthesis. IEEE Nanotechnology Magazine, 2013, 12, 649-655.	2.0	7
172	Noise Properties of ZnO Nanowalls Deposited Using Rapid Thermal Evaporation Technology. IEEE Photonics Technology Letters, 2013, 25, 213-216.	2.5	7
173	Effects of Initial GaN Growth Mode on Patterned Sapphire on the Opto-Electrical Characteristics of GaN-Based Light-Emitting Diodes. Journal of Display Technology, 2013, 9, 292-296.	1.2	7
174	GaN Nanowire Field Emitters With the Adsorption of Au Nanoparticles. IEEE Electron Device Letters, 2013, 34, 553-555.	3.9	7
175	GaN-Based High-Voltage Light-Emitting Diodes With SU-8 Passivation. Journal of Display Technology, 2015, 11, 374-377.	1.2	7
176	Conversion Efficiency Improvement of InGaN/GaN Multiple-Quantum-Well Solar Cells With <italic>Ex Situ</italic> AlN Nucleation Layer. IEEE Transactions on Electron Devices, 2015, 62, 1473-1477.	3.0	7
177	Enhanced Photoluminescent Properties and Crystalline Morphology of LiBaPO4:Tm3+ Phosphor through Microwave Sintering Method. Materials, 2016, 9, 356.	2.9	7
178	Preparation of a Carbon Doped Tissue-Mimicking Material with High Dielectric Properties for Microwave Imaging Application. Materials, 2016, 9, 559.	2.9	7
179	Indium Aluminum Zinc Oxide Thin Film Transistor With Al₂O₃ Dielectric for UV Sensing. IEEE Photonics Technology Letters, 2019, 31, 1005-1008.	2.5	7
180	Photoresponses of Zinc Tin Oxide Thin-Film Transistor. Journal of Nanoscience and Nanotechnology, 2020, 20, 1704-1708.	0.9	7

#	Article	IF	Citations
181	High electrostatic discharge protection of InGaN/GaN MQW LEDs by using GaN Schottky diodes. Physica Status Solidi A, 2003, 200, 91-94.	1.7	6
182	AlGaN Ultraviolet Metalâ€“Semiconductorâ€“Metal Photodetectors with Low-Temperature-Grown Cap Layers. Japanese Journal of Applied Physics, 2007, 46, 2471-2473.	1.5	6
183	GaN-Based Power Flip-Chip LEDs With Cu Submount. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1287-1291.	2.9	6
184	The Bias-Crystallization Mechanism on Structural Characteristics and Electrical Properties of Zn-In-Sn-O Film. Materials Transactions, 2011, 52, 1560-1564.	1.2	6
185	InGaN metal-semiconductor-metal photodetectors with triethylgallium precursor and unactivated Mg-doped GaN cap layers. Journal of Applied Physics, 2011, 110, .	2.5	6
186	Effect of surface modification by self-assembled monolayer on the ZnO film ultraviolet sensor. Applied Physics Letters, 2013, 103, 022101.	3.3	6
187	Synchrotron radiation based cross-sectional scanning photoelectron microscopy and spectroscopy of n-ZnO:Al/p-GaN:Mg heterojunction. Applied Physics Letters, 2013, 102, .	3.3	6
188	A triband bandpass filter with low loss and high band selectivity using the splitâ€end asymmetric stepped impedance resonators. Microwave and Optical Technology Letters, 2014, 56, 1427-1430.	1.4	6
189	Investigation of optical and electrical properties of GaN-based blue light-emitting diodes with various quantum well thicknesses. Journal of Photonics for Energy, 2015, 5, 057612.	1.3	6
190	Effects of microcell layout on the performance of GaN-based high-voltage light-emitting diodes. Journal of Photonics for Energy, 2015, 5, 057605.	1.3	6
191	Bandgap Engineered Ultraviolet Photodetectors with Gallium-Zinc-Oxide via Co-Sputtering Method. ECS Journal of Solid State Science and Technology, 2018, 7, Q3083-Q3088.	1.8	6
192	UV-Enhanced 2-D Nanostructured ZnO Field Emitter With Adsorbed Pt Nanoparticles. IEEE Electron Device Letters, 2018, 39, 1932-1935.	3.9	6
193	Voltage-Tunable UVCâ€“UVB Dual-Band Metalâ€“Semiconductorâ€“Metal Photodetector Based on Ga2O3/MgZnO Heterostructure by RF Sputtering. Coatings, 2020, 10, 994.	2.6	6
194	Aluminum-doped zinc oxide nanorods and methyl alcohol gas sensor application. Microsystem Technologies, 2022, 28, 377-382.	2.0	6
195	Growth of InGaN self-assembled quantum dots and their application to photodiodes. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 792.	2.1	5
196	Room temperature photo-CVD SiO2layers on AlGaN and AlGaN/GaN MOS-HFETs. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 404-409.	1.8	5
197	Isopropyl Alcohol Sensors of CuO Nanotubes by Thermal Oxidation of Copper Films on Glass. IEEE Sensors Journal, 2011, 11, 3276-3282.	4.7	5
198	Effect of Varied Undoped GaN Thickness on ESD and Optical Properties of GaN-Based LEDs. IEEE Photonics Technology Letters, 2012, 24, 800-802.	2.5	5

#	Article	IF	Citations
199	GaN-Based LEDs With an HT-AlN Nucleation Layer Prepared on Patterned Sapphire Substrate. IEEE Photonics Technology Letters, 2013, 25, 88-90.	2.5	5
200	GaN-Based Light-Emitting Diodes on Electrochemically Etched ${m n}^{-}$-GaN Template. IEEE Photonics Technology Letters, 2013, 25, 1531-1534.	2.5	5
201	GaN-Based LEDs With Hot/Cold Factor Improved by the Electron Blocking Layer. Journal of Display Technology, 2014, 10, 1078-1082.	1.2	5
202	A compact lowâ€pass filter with ultrabroad stopband characteristics. Microwave and Optical Technology Letters, 2015, 57, 2800-2803.	1.4	5
203	Effect of different alkali carbonate on the microstructure and photoluminescent properties of YInGe2O7:Eu3+ phosphors. Journal of Materials Science: Materials in Electronics, 2016, 27, 2963-2967.	2.2	5
204	Visible Illumination Enhanced Nonenzymatic Glucose Photobiosensor Based on TiO₂ Nanorods Decorated With Au Nanoparticles. IEEE Transactions on Biomedical Engineering, 2018, 65, 2052-2057.	4.2	5
205	Fabrication of Zinc Oxide-Based Thin-Film Transistors by Radio Frequency Sputtering for Ultraviolet Sensing Applications. Journal of Nanoscience and Nanotechnology, 2018, 18, 3518-3522.	0.9	5
206	Relaxation time of polymer ball type PDLC films. Liquid Crystals, 1996, 21, 707-711.	2.2	4
207	A novel waveguide structure to reduce beam divergence and threshold current in GaInP/AlGaInP visible quantum-well lasers. Applied Physics Letters, 1997, 71, 2245-2247.	3.3	4
208	Reactive ion etching for AlGaInP/GaInP laser structures. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 2031-2036.	2.1	4
209	Si field-effect transistor with doping dipole in buffer layer. Applied Physics Letters, 1999, 75, 2848-2850.	3.3	4
210	Ion-implantation technology for improved GaAs MESFETs performance. Journal of Materials Science: Materials in Electronics, 2004, 15, 91-93.	2.2	4
211	GaN-Based LEDs With Air Voids Prepared by Laser Scribing and Chemical Etching. IEEE Photonics Technology Letters, 2011, 23, 1172-1174.	2.5	4
212	Characteristics of GaN/InGaN Double-Heterostructure Photovoltaic Cells. International Journal of Photoenergy, 2012, 2012, 1-5.	2.5	4
213	Enhanced Current Spreading for GaN-Based Side-View LEDs by Adding an Metallic Stripe Across the Long Side of the Chip. IEEE Photonics Technology Letters, 2012, 24, 1412-1414.	2.5	4
214	Electron field emitters made of 3-D CuO nanowires on flexible silicon substrate fabricated by heating Cu rods with through silicon via process. RSC Advances, 2016, 6, 47292-47297.	3.6	4
215	Enhanced Detection of Ethanol in a Humid Ambient Using Al₂O₃-Doped Cactus-Like ZnO Nanoflowers With Gold Nanoparticles. IEEE Transactions on Device and Materials Reliability, 2019, 19, 409-415.	2.0	4
216	The study of humidity sensor based on Li-doped ZnO nanorods by hydrothermal method. Microsystem Technologies, 2022, 28, 423-427.	2.0	4

#	Article	IF	Citations
217	Investigation of Conductive Mechanism of Amorphous IGO Resistive Random-Access Memory with Different Top Electrode Metal. Coatings, 2020, 10, 504.	2.6	4
218	Stability-Enhanced Resistive Random-Access Memory via Stacked In_xGa_{1â€“x}O by the RF Sputtering Method. ACS Omega, 2021, 6, 10691-10697.	3.5	4
219	Advanced Nanomaterials for Applications in Photonic and Sensor Devices. Journal of Nanomaterials, 2022, 2022, 1-2.	2.7	4
220	Economical Passive Filter Synthesis Using Genetic Programming Based on Tree Representation. , 0, , .		3
221	Nitride-Based Schottky Barrier Sensor Module With High Electrostatic Discharge Reliability. IEEE Photonics Technology Letters, 2007, 19, 717-719.	2.5	3
222	Enhancement of CMOSFETs Performance by Utilizing SACVD-Based Shallow Trench Isolation for the 40-nm Node and Beyond. IEEE Nanotechnology Magazine, 2011, 10, 433-438.	2.0	3
223	GaN Schottky Barrier Photodetectors With a Lattice-Matched ${m Al}_{0.82}{m In}_{0.18}{m N}$ Intermediate Layer. IEEE Sensors Journal, 2011, 11, 2895-2901.	4.7	3
224	High-Performance a-IGZO Thin-Film Transistor with Organic Polymer Dielectric Layer. , 2011, , .		3
225	AlGaN/GaN metal-insulator-semiconductor heterostructure field-effect transistor with an in-situ AlN cap layer. Applied Physics Letters, 2011, 99, 153505.	3.3	3
226	Microstructural Characteristics of InGaZnO Thin Film Using an Electrical Current Method. Materials Transactions, 2012, 53, 733-738.	1.2	3
227	The Effects of Crystallization on Mechanical Mechanism and Residual Stress of Sputtered Ag Thin Films. Materials Transactions, 2012, 53, 2049-2055.	1.2	3
228	UV Enhanced Field Emission for Î²-Ga2O3 Nanowires. IEEE Electron Device Letters, 2013, 34, 701-703.	3.9	3
229	Integration of a-IGZO Thin-Film Transistor and Crystalline-Si Interdigitated Back Contact Photovoltaic Cell With 3D Stacking Structure as Self-Powered Solar Switch. IEEE Electron Device Letters, 2014, 35, 1040-1042.	3.9	3
230	GaN-Based Light-Emitting Diodes With Staircase Electron Injector Structure. Journal of Display Technology, 2014, 10, 162-166.	1.2	3
231	GaN-Based Power Flip-Chip LEDs With SILAR and Hydrothermal ZnO Nanorods. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 431-435.	2.9	3
232	Enhanced field emission properties based on Inâ€“In2O3 composite nanopagodas. RSC Advances, 2015, 5, 5192-5196.	3.6	3
233	Through-silicon via submount for the CuO/Cu2O nanostructured field emission display. RSC Advances, 2018, 8, 706-709.	3.6	3
234	Amorphous Indium Titanium Zinc Oxide Thin Film Transistor and Impact of Gate Dielectrics on Its Photo-Electrical Properties. ECS Journal of Solid State Science and Technology, 2018, 7, Q3049-Q3053.	1.8	3

#	Article	IF	Citations
235	Bandgap-Engineered Zinc-Tin-Oxide Thin Films for Ultraviolet Sensors. Journal of Nanoscience and Nanotechnology, 2018, 18, 4930-4934.	0.9	3
236	Investigation of nitrogen doping effects on light-induced oxygen vacancy ionization and oxygen desorption in c-IGO TFTs. Materials Research Express, 2019, 6, 106445.	1.6	3
237	Indium Aluminum Zinc Oxide Phototransistor With HfO2 Dielectric Layer Through Atomic Layer Deposition. IEEE Sensors Journal, 2020, 20, 1838-1842.	4.7	3
238	Fabrication of Silicon Dioxide by Photo-Chemical Vapor Deposition to Decrease Detector Current of ZnO Ultraviolet Photodetectors. ACS Omega, 2020, 5, 27566-27571.	3.5	3
239	Polycrystalline Inâ€“Gaâ€“O Thin-Film Transistors Coupled With a Nitrogen Doping Technique for High-Performance UV Detectors. IEEE Transactions on Electron Devices, 2020, 67, 140-145.	3.0	3
240	Polymer dispersed liquid crystal display device for projection high definition television application. Macromolecular Symposia, 1994, 84, 159-166.	0.7	2
241	Nitride-based near-ultraviolet multiple-quantum well light-emitting diodes with AlGaN barrier layers. Journal of Electronic Materials, 2003, 32, 415-418.	2.2	2
242	InGaN/GaN multi-quantum dot light-emitting diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2405-2408.	0.8	2
243	A Ka-band PHEMT diode double-balanced star mixer MMIC. Microwave and Optical Technology Letters, 2004, 42, 455-458.	1.4	2
244	Effect of Au distribution in NiO/Au film on the ohmic contact formation to p-type GaN. Journal of Materials Research, 2005, 20, 456-463.	2.6	2
245	Practical impedance matching using genetic programming. Microwave and Optical Technology Letters, 2006, 48, 375-377.	1.4	2
246	Nonâ€lithographic nanopatterning of InGaN/GaN multiple quantum well nanopillars by focused ion beams. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2186-2188.	0.8	2
247	The challenge of commercialized crystalline silicon solar cell. , 2008, , .		2
248	ZnO nanowire-based oxygen gas sensor. , 2008, , .		2
249	A novel miniature dual-mode filter based on modified sierpinski fractal resonator. , 2008, , .		2
250	III-Nitride Schottky Rectifiers With an AlGaN/GaN/AlGaN/GaN Quadruple Layer and Their Applications to UV Detection. IEEE Sensors Journal, 2010, 10, 799-804.	4.7	2
251	Temperature Dependence of Electrical Characteristics of Strained nMOSFETs Using Stress Memorization Technique. IEEE Electron Device Letters, 2011, 32, 835-837.	3.9	2
252	Growth and Photoelectric Properties of Twinned ZnSe$_{m {1-x}}$Te$_{m x}$ Nanotips. IEEE Nanotechnology Magazine, 2011, 10, 379-384.	2.0	2

#	Article	IF	Citations
253	Applications of Advanced Nanomaterials to Microelectronic and Photonic Devices. Journal of Nanomaterials, 2015, 2015, 1-1.	2.7	2
254	Terahertz Negative Refraction in a High-Temperature Superconducting Material. IEEE Transactions on Terahertz Science and Technology, 2015, 5, 230-235.	3.1	2
255	Design of wideband bandpass filter using mode-exciting technology. Microwave and Optical Technology Letters, 2016, 58, 1507-1510.	1.4	2
256	Optical and photo-electrical properties of zinc tin oxide thin-film phototransistor. , 2018, , .		2
257	Design of Dual-Band Transparent Antenna by Using Nano-Structured Thin Film Coating Technology. , 2018, , .		2
258	An Amorphous (Al0.12Ga0.88)2O3 Deep Ultraviolet Photodetector. IEEE Photonics Journal, 2020, 12, 1-8.	2.0	2
259	The Characteristics of Aluminum-Gallium-Zinc-Oxide Ultraviolet Phototransistors by Co-Sputtering Method. Electronics (Switzerland), 2021, 10, 631.	3.1	2
260	Performance Improvement of Co-Sputtering AlGaZnO Solar-Blind Photodetectors. IEEE Sensors Journal, 2021, 21, 18682-18687.	4.7	2
261	High efficiency transparent digital television antenna based on nano-structured thin film coating technology. , 2017, , .		2
262	Photoluminescence of Erbium Implanted in SiGe. Materials Research Society Symposia Proceedings, 1996, 422, 131.	0.1	1
263	Studies of polymer ball type polymer dispersed liquid crystal films. Materials Research Society Symposia Proceedings, 1996, 425, 287.	0.1	1
264	A three-stage Ka band PHEMT wideband amplifier MMIC. Microwave and Optical Technology Letters, 2004, 42, 277-280.	1.4	1
265	Influences of<tex>$delta $</tex>-Doping Position on the Characteristics of SiGeâ€“Si DCFETs. IEEE Electron Device Letters, 2004, 25, 477-479.	3.9	1
266	Ka-band 1-W PHEMT MMIC power amplifiers on 2mil-thick GaAs substrates. Microwave and Optical Technology Letters, 2005, 45, 181-185.	1.4	1
267	Improved External Quantum Efficiency of GaN p-i-n Photodiodes With a TiO$_{2}$ Roughened Surface. IEEE Photonics Technology Letters, 2008, 20, 285-287.	2.5	1
268	GaN photodetectors prepared on silicon and sapphire substrates. , 2008, , .		1
269	High-Sensitivity Nitride-Based Ultraviolet Photosensors with a Low-Temperature AlGaN Interlayer. Journal of Electronic Materials, 2010, 39, 29-33.	2.2	1
270	Improvement of Poly-Pimple-Induced Device Mismatch on 6T-SRAM at 65-nm CMOS Technology. IEEE Transactions on Electron Devices, 2010, 57, 956-959.	3.0	1

#	Article	IF	Citations
271	Growth and Characterization of ZnSe/CdSe Multiquantum Disks. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 779-784.	2.9	1
272	Characteristics of Thin-Film-Transistors Based on Zn–In–Sn–O Thin Films Prepared by Co-Sputtering System. Materials Transactions, 2012, 53, 571-574.	1.2	1
273	Investigation of Ni/Ag contact to pâ€GaN with an O₂ plasma treatment and its application to GaNâ€based LEDs. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1568-1574.	1.8	1
274	Infrared Tunable Multichannel Filter in a Doped Semiconductor-Dielectric Photonic Crystal Heterostructure. IEEE Journal of Quantum Electronics, 2012, 48, 361-366.	1.9	1
275	Electron-Field-Emission Properties of Gallium Compound by Ammonification of Ga ₂O$_{3}$ Nanowires. IEEE Nanotechnology Magazine, 2013, 12, 692-695.	2.0	1
276	GaN-Based Light-Emitting Diodes With Step Graded-Refractive Index $({hbox{ZnO}})_{x}({hbox{SiO}}_{2})_{1-x}$ Micropillar Array. Journal of Display Technology, 2013, 9, 353-358.	1.2	1
277	Characteristics of TiO<inf>2</inf> metal-semiconductor-metal photodetectors with O<inf>2</inf> plasma treatment. , 2014, , .		1
278	A high selectivity and wide stopband UWB bandpass filter using asymmetric SIRs with splitâ€end. Microwave and Optical Technology Letters, 2014, 56, 1353-1356.	1.4	1
279	c-Si solar cells and Si n-MOSFETs prepared by ICP assisted hot wire implantation doping. RSC Advances, 2015, 5, 96547-96550.	3.6	1
280	Effect of Solvent Chelating on Crystal Growth Mechanism of CZTSe Nanoink in Polyetheramine. IEEE Nanotechnology Magazine, 2015, 14, 896-903.	2.0	1
281	p-MOSFET and n-MOSFET prepared by ICP-assisted hot wire implantation doping technique. IEEE Electron Device Letters, 2016, , 1-1.	3.9	1
282	Growth and characterization of high quality N-type GaSb/GaAs heterostructure by IMF growth mode using MOCVD for low power application. Applied Physics Letters, 2017, 111, 162108.	3.3	1
283	The Effect of the Thickness and Oxygen Ratio Control of Radio-Frequency Magnetron Sputtering on MgZnO Thin-Film Transistors. Journal of Nanoscience and Nanotechnology, 2017, 17, 2037-2040.	0.9	1
284	Photoresponses of Gallium Zinc Tin Oxide Thin-Film Transistors Fabricated by Cosputtering Method. , 2018, 2, 1-4.		1
285	Effects of Average Power-Handling Capability on DC-Sputtering Aluminum Nitride Thin Film on Ceramic Substrate. , 2018, , .		1
286	High Response of Ethanol Gas Sensor Based on NiO-Doped Apple Pectin by the Solution Process. Coatings, 2021, 11, 1073.	2.6	1
287	Properties of Gaâ€“Znâ€“O Ultraviolet Phototransistors Using Radio-Frequency Magnetron Co-Sputtering Method. Nanoscience and Nanotechnology Letters, 2018, 10, 396-402.	0.4	1
288	Neodymium-doped GaAs Light-emitting Diodes. Materials Research Society Symposia Proceedings, 1996, 422, 351.	0.1	0

#	Article	IF	Citations
289	InGaN/GaN LEDs with a Si-doped InGaN/GaN short-period superlattice tunneling contact layer. Journal of Electronic Materials, 2003, 32, 411-414.	2.2	0
290	Imapct of SiN on Performance in Novel CMOS Architecture Using Substrate Strained-SiGe and Mechanical Strained-Si Technology. , 0, , .		0
291	Strained-Si nMOSFETs with Ni Silicide. , 0, , .		0
292	Nitride-based light emitting diodes with quaternary p-AlInGaN surface layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2153-2155.	0.8	0
293	Controlled Self-formation of GaN Nanotubes by Inductively Coupled Plasmas Etching. , 2006, , .		0
294	Inductively coupled plasma etching of Si1â^'xGex in CF4â^•Ar and Cl2â^•Ar discharges. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 728-731.	2.1	0
295	Strained-Si nMOSFETs with Ni Silicide. , 2006, , .		0
296	Imapct of SiN on Performance in Novel CMOS Architecture Using Substrate Strained-SiGe and Mechanical Strained-Si Technology. , 2006, , .		0
297	High Performance InGaAs PIN Photodetector. , 2007, , .		0
298	InGaN/GaN MQW structures prepared with various In and Ga flow rates. International Journal of Electronics, 2007, 94, 1-7.	1.4	0
299	GaN Schottky barrier photodetectors with multi-MgN/GaN buffer. , 2008, , .		0
300	High temperature characteristics of ZnO-based MOS-FETs with photochemical vapor deposition SiO<inf>2</inf> gate oxide. , 2009, , .		0
301	Quaternary AlInGaN photodetectors with MIS structure. , 2009, , .		0
302	Two-Step Etching Mechanism of Ag-Si Nanostructure with Various Ag Nanoshape Depositions. Materials Transactions, 2009, 50, 1992-1997.	1.2	0
303	ZnSe/ZnCdSeTe Superlattice Nanotips. IEEE Nanotechnology Magazine, 2011, 10, 682-687.	2.0	0
304	GaN-Based LEDs with a Mirror Structure and an Insulating Layer. , 2012, , .		0
305	In situ grown AlN/AlGaN/GaN heterostructure field-effect transistor. , 2012, , .		0
306	Back Cover: Investigation of Ni/Ag contact to pâ€GaN with an O‹sub›2‹/sub› plasma treatment and its application to GaNâ€based LEDs (Phys. Status Solidi A 8/2012). Physica Status Solidi (A) Applications and Materials Science, 2012, 209, .	1.8	0

#	Article	IF	Citations
307	A Si Nanowire Photovoltaic Device Prepared by Selective Electroless Etching. IEEE Nanotechnology Magazine, 2012, 11, 1148-1150.	2.0	0
308	Improved efficiency of p-type quasi-mono silicon blanket emitter solar cell by ion implantation and backside rounding. Materials Science-Poland, 2013, 31, 516-524.	1.0	0
309	Frequency Response of a Ferroelectric Material in Double-Negative Region. IEEE Photonics Journal, 2014, 6, 1-11.	2.0	0
310	GaN-Based Light-Emitting-Diode With a p-InGaN Layer. Journal of Display Technology, 2014, 10, 204-207.	1.2	0
311	Effect of V/III ratios on surface morphology in a GaSb thin film grown on GaAs substrate by MOCVD. , 2014, , .		0
312	Assessment of dielectric properties for the microwave phantom production. , 2015, , .		0
313	InGaN-based MQE LEDs with tunnel-junction-cascaded structure. , 2015, , .		0
314	GaN-based LEDs with flower shape ZnO nanorods by SILAR-based and hydrothermal methods. , 2015, , .		0
315	Transmission Properties in Lossy Single-Negative Materials. IEEE Photonics Journal, 2015, 7, 1-8.	2.0	0
316	An excellent encapsulation of silicone on an optimized-ZnO-nanowires anti-reflection layer for crystalline-Si photovoltaic devices. , 2015, , .		0
317	Effects of last barrier thickness on the hotâ€“cold factor of GaN-based light-emitting diodes. Journal of Photonics for Energy, 2015, 5, 057602.	1.3	0
318	AlGaInP-based LEDs with ZnO nanostructures by successive ionic layer adsorption and reaction and hydrothermal methods. , 2015, , .		0
319	Fabrication and characterization of GaN ultraviolet photodetector prepared by growing on geometrical patterned sapphire substrate. , 2016, , .		0
320	A three-dimensional ZnO nanowires photodetector. , 2016, , .		0
321	Performance improvement of highly mismatched GaSb layers on GaAs by interfacial-treatment-assisted chemical vapor deposition. Journal of Materials Science: Materials in Electronics, 2017, 28, 845-855.	2.2	0
322	System setup consideration for range gated imaging. , 2017, , .		0
323	Detection Method of Alcohol in Calf Serum with Zinc Oxide Nanowire Ethanol Sensor. Journal of Nanoscience and Nanotechnology, 2017, 17, 2104-2108.	0.9	0
324	Effect of different partial pressure on Ga-doped ZnO UV photodetectors by RF sputtering. , 2018, , .		0

#	Article	IF	Citations
325	Selected Papers from IEEE ICASI 2018. Applied Sciences (Switzerland), 2020, 10, 964.	2.5	0
326	Imapct of SiN on Performance in Novel CMOS Architecture Using Substrate Strained-SiGe and Mechanical Strained-Si Technology. , 0, , .		0
327	Strained-Si nMOSFETs with Ni Silicide. , 0, , .		0